

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE

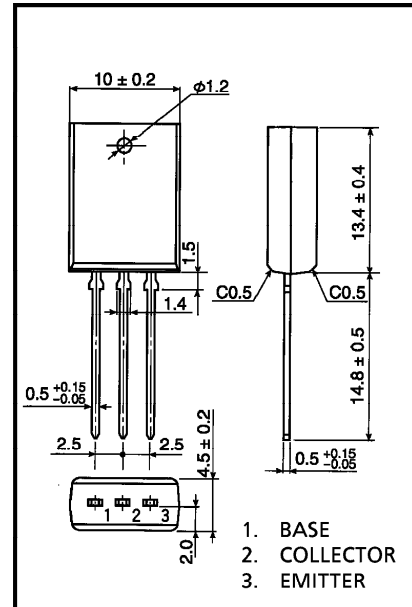
2SD2526

HIGH POWER SWITCHING APPLICATIONS

HAMMER DRIVE, PULSE MOTOR DRIVE APPLICATIONS

- High DC Current Gain : $h_{FE} = 2000$ (Min.) ($V_{CE} = 3V, I_C = 3A$)
- Low Saturation Voltage : $V_{CE(sat)} = 1.5V$ (Max.) ($I_C = 3A$)
- Complementary to 2SB1641

Unit in mm



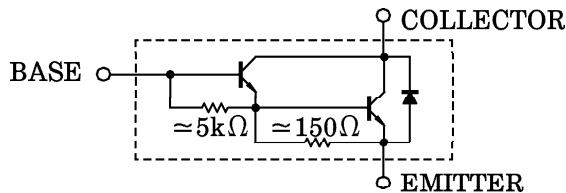
MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	100	V
Collector-Emitter Voltage		V_{CEO}	100	V
Emitter-Base Voltage		V_{EBO}	7	V
Collector Current	DC	I_C	5	A
	Pulse		8	
Base Current		I_B	0.5	A
Collector Power Dissipation		P_C	1.8	W
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	-55~150	°C

JEDEC	—
EIAJ	—
TOSHIBA	2-10T1A

Weight : 1.5g

EQUIVALENT CIRCUIT



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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	$V_{CB} = 100V, I_E = 0$	—	—	100	μA
Emitter Cut-off Current		I_{EBO}	$V_{EB} = 6V, I_C = 0$	—	—	2.5	mA
Collector-Emitter Breakdown Voltage		$V_{(BR) CEO}$	$I_C = 30mA, I_B = 0$	100	—	—	V
DC Current Gain		$h_{FE} (1)$	$V_{CE} = 3V, I_C = 3A$	2000	—	15000	
		$h_{FE} (2)$	$V_{CE} = 3V, I_C = 5A$	1000	—	—	
Collector-Emitter Saturation Voltage		$V_{CE (sat) (1)}$	$I_C = 3A, I_B = 6mA$	—	1.1	1.5	V
		$V_{CE (sat) (2)}$	$I_C = 5A, I_B = 20mA$	—	1.3	2.5	
Base-Emitter Saturation Voltage		$V_{BE (sat)}$	$I_C = 3A, I_B = 6mA$	—	1.7	2.5	V
Switching Time	Turn-on Time	t_{on}	<p>$I_{B1} = -I_{B2} = 6mA$ DUTY CYCLE $\leq 1\%$ $V_{CC} = 30V$</p>	—	1.0	—	μs
	Storage Time	t_{stg}		—	4.0	—	
	Fall Time	t_f		—	2.5	—	

